

SANYO

No.1049D

2SA1253/2SC3135

PNP/ NPN Epitaxial Planar Silicon Transistors

High- h_{FE} , AF Amp Applications**Features**

- High V_{EBO}
- Wide ASO and high durability against breakdown

(): 2SA1253

Absolute Maximum Ratings/ $T_a = 25^\circ\text{C}$

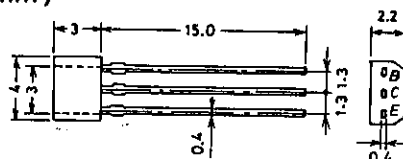
			unit
Collector to base voltage	V_{CBO}	(-) 60	V
Collector to emitter voltage	V_{CEO}	(-) 50	V
Emitter to base voltage	V_{EBO}	(-) 15	V
Collector current	I_C	(-) 200	mA
Collector Current(Pulse)	I_{CP}	(-) 400	mA
Collector dissipation	P_C	250	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to $+150$	$^\circ\text{C}$

Electrical Characteristics/ $T_a = 25^\circ\text{C}$

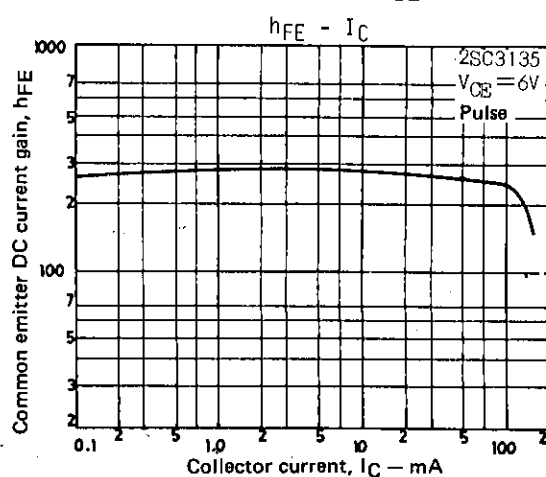
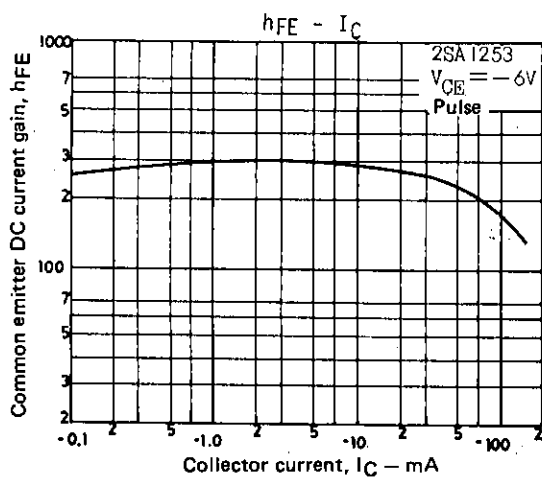
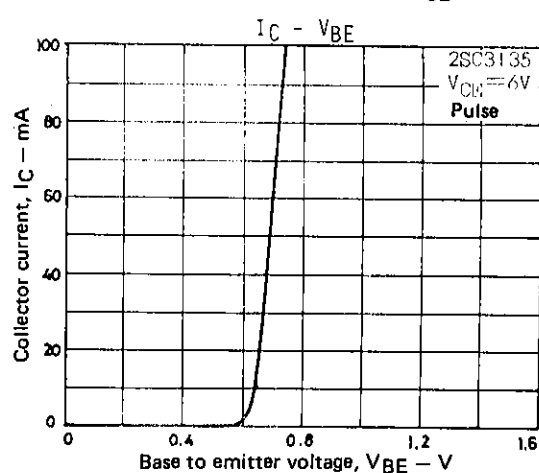
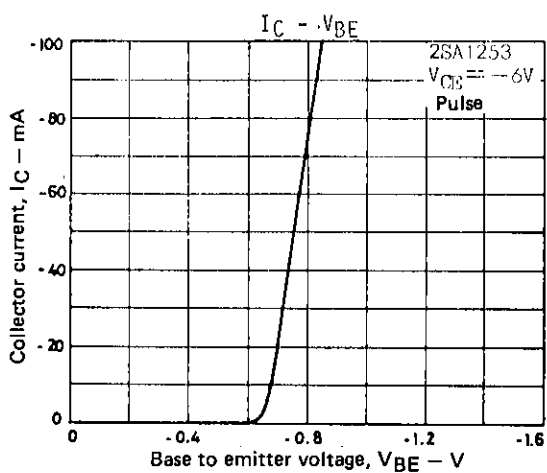
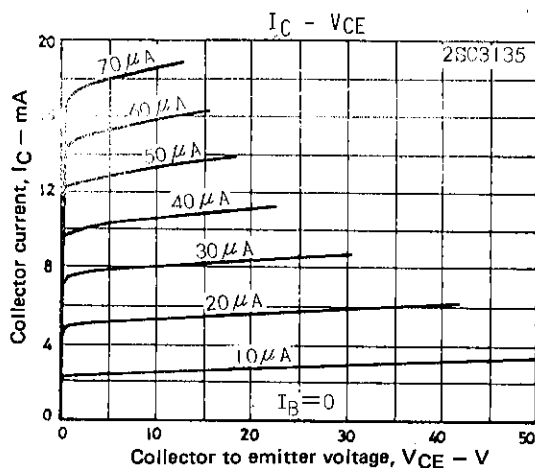
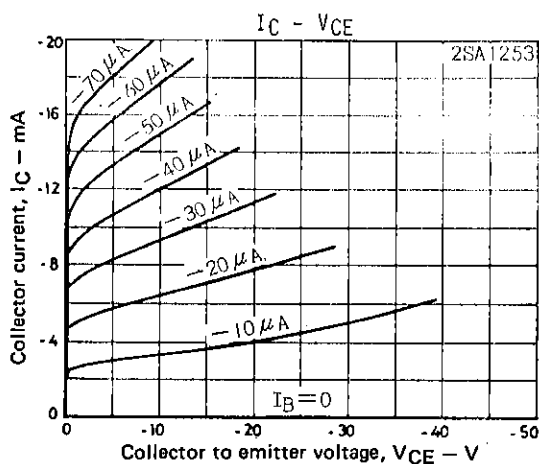
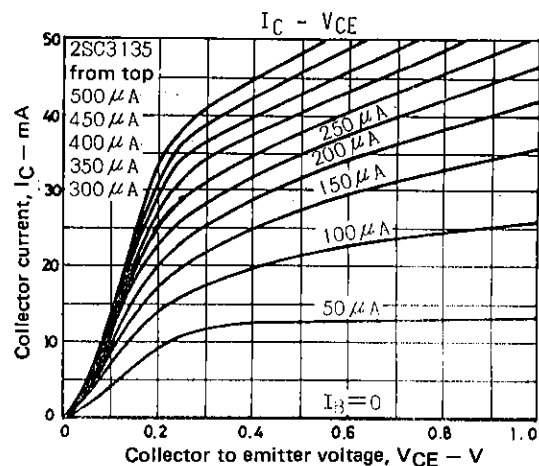
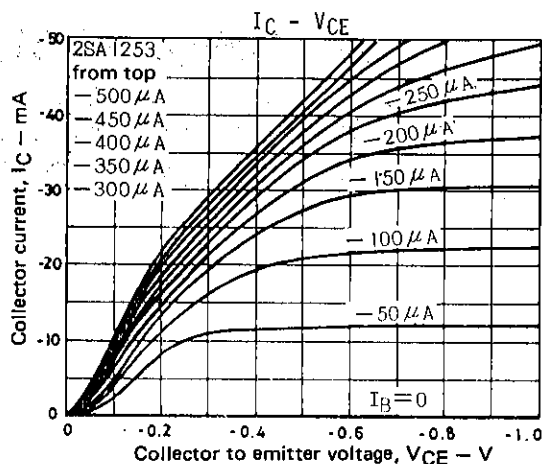
			min	typ	max	unit
Collector cutoff current	I_{CBO}	$V_{CB} = (-)40\text{V}, I_E = 0$			(-) 0.1	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = (-)10\text{V}, I_C = 0$			(-) 0.1	μA
DC current gain	h_{FE}	$V_{CE} = (-)6\text{V}, I_C = (-)1\text{mA}$	100^*		560^*	
Gain-bandwidth product	f_T	$V_{CE} = (-)6\text{V}, I_C = (-)1\text{mA}$		100		MHz
Common base output capacitance	c_{ob}	$V_{CB} = (-)6\text{V}, f = 1\text{MHz}$		(3.8)		pF
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = (-)50\text{mA}, I_B = (-)5\text{mA}$		(-0.2)	(-0.5)	V
Collector to base breakdown voltage	$V_{(BR)CBO}$	$I_C = (-)10\mu\text{A}, I_E = 0$	(-60)			V
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = (-)1\text{mA}, R_{BE} = \infty$	(-50)			V
Emitter to base breakdown voltage	$V_{(BR)EBO}$	$I_E = (-)10\mu\text{A}, I_C = 0$	(-15)			V

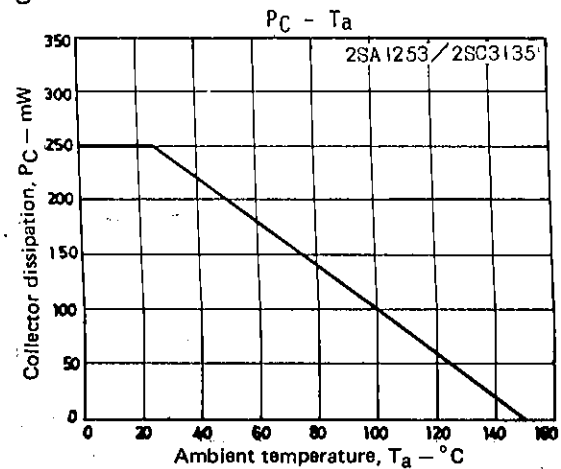
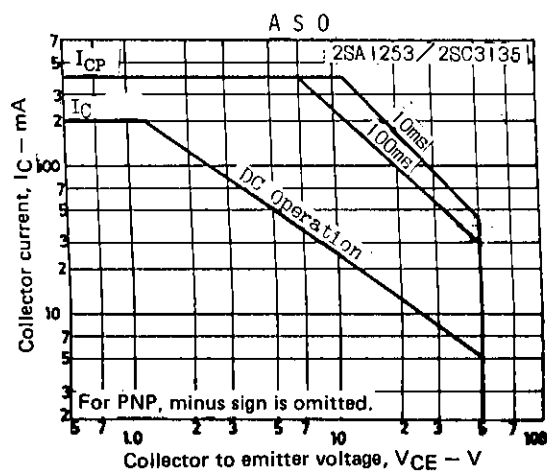
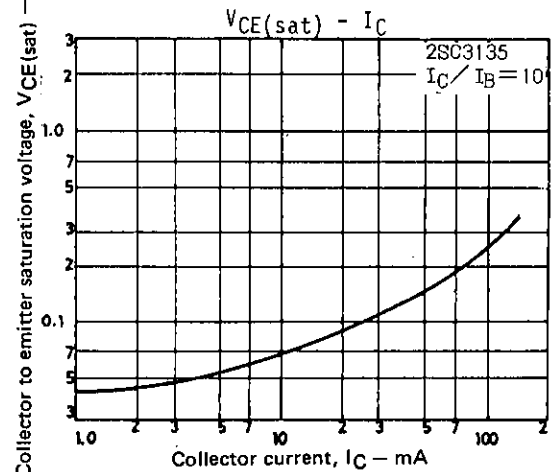
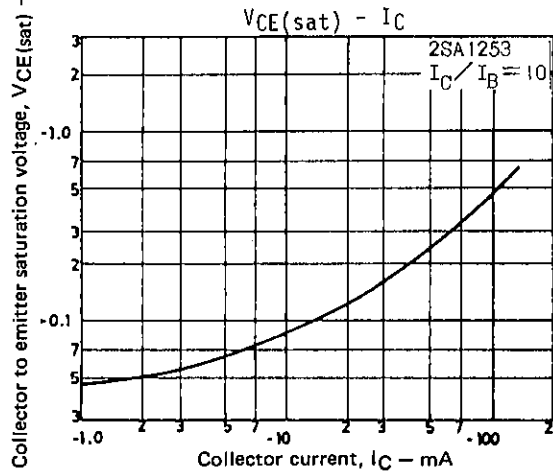
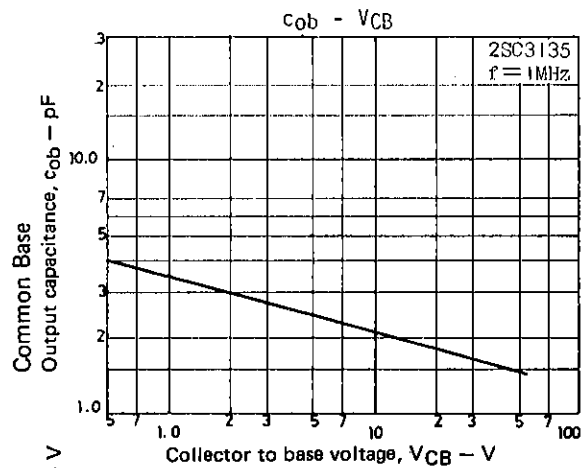
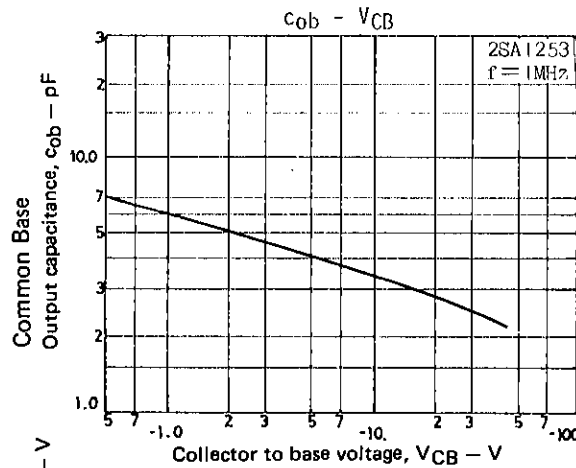
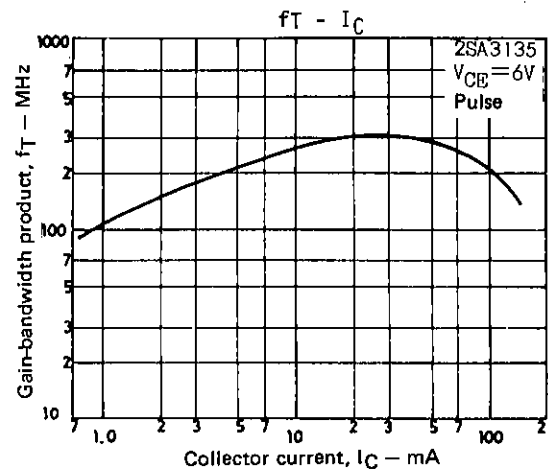
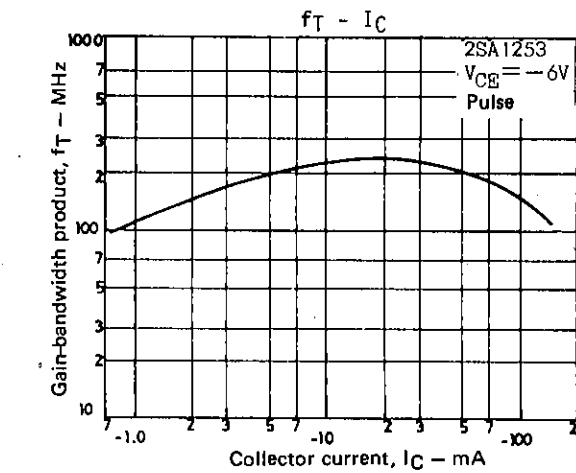
* The 2SA1253/2SC3135 are classified by 1 mA h_{FE} as follows:

100	R	200	140	S	280	200	T	400	280	U	560
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Package Dimensions 2033
(unit: mm)

B: Base
C: Collector
E: Emitter
SANYO: SPA





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